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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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# 2SC4702

# Silicon NPN Epitaxial



ADE-208-1120A (Z) 2nd. Edition Mar. 2001

### **Application**

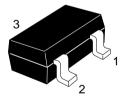
High voltage amplifier

### **Features**

- High breakdown voltage
   V<sub>CEO</sub> = 300 V
- Small Cob Cob = 1.5 pF Typ.

### **Outline**

**MPAK** 



- 1. Emitter
- 2. Base
- 3. Collector

Note: Marking is "XV-".

# 2SC4702

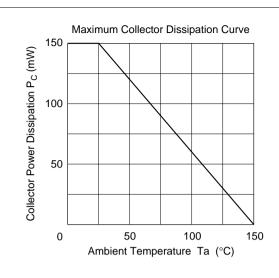
## **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

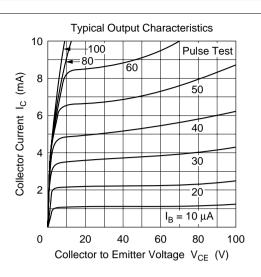
Item	Symbol	Ratings	Unit	
Collector to base voltage	$V_{CBO}$	300	V	
Collector to emitter voltage	$V_{\text{CEO}}$	300	V	
Emitter to base voltage	$V_{EBO}$	5	V	
Collector current	I <sub>c</sub>	50	mA	
Collector power dissipation	P <sub>c</sub>	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

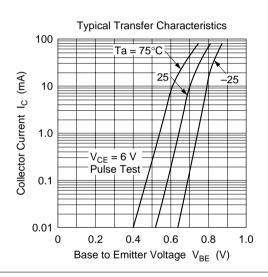
### **Electrical Characteristics** (Ta = 25°C)

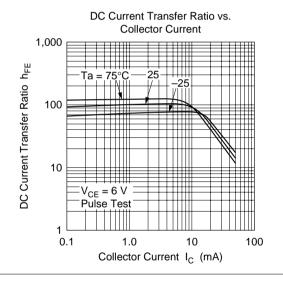
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	300	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	300	_	_	V	$I_{\rm C}$ = 1 mA, $R_{\rm BE}$ =
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	0.1	μA	V <sub>CB</sub> = 250 V, I <sub>E</sub> = 0
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	0.5	V	$I_{\rm C} = 30 \text{ mA}, I_{\rm B} = 3 \text{ mA}$
DC current transfer ratio	h <sub>FE</sub>	60	_	150		$V_{CE} = 6 \text{ V}, I_{C} = 2 \text{ mA}$
Gain bandwidth product	f <sub>T</sub>	_	80	_	MHz	$V_{CE} = 6 \text{ V}, I_{C} = 5 \text{ mA}$
Collector output capacitance	Cob	_	1.5	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$



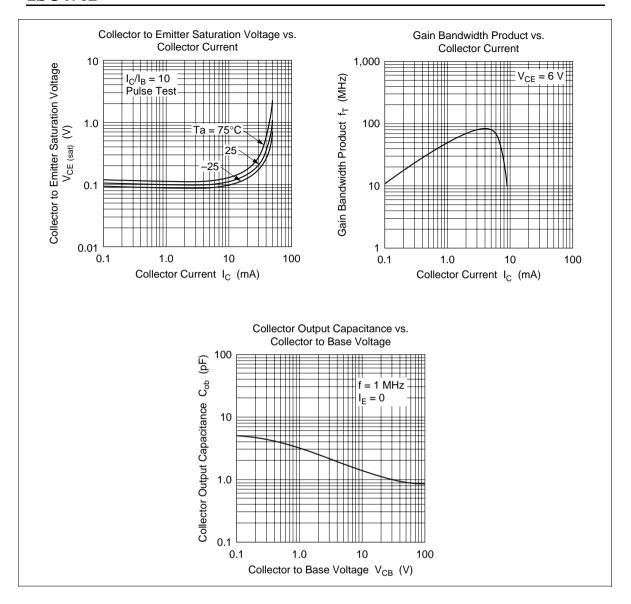




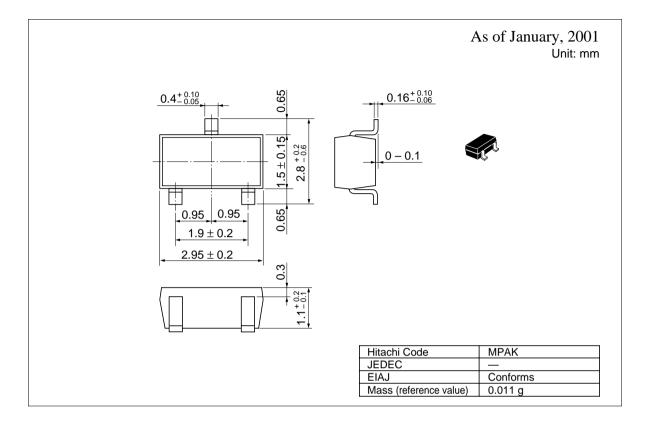




## 2SC4702



### **Package Dimensions**



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Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

**URL** NorthAmerica http://semiconductor.hitachi.com/ http://www.hitachi-eu.com/hel/ecg Europe Asia http://sicapac.hitachi-asia.com

http://www.hitachi.co.jp/Sicd/indx.htm Japan

#### For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Germany

Hitachi Europe GmbH Electronic Components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Fax: <1>(408) 433-0223 Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead

Berkshire SL6 8YA, United Kingdom Tel: <886>-(2)-2718-3666 Tel: <44> (1628) 585000 Fax: <44> (1628) 585160

Hitachi Asia Ltd. Hitachi Tower 16 Collyer Quay #20-00, Singapore 049318 Tel: <65>-538-6533/538-8577 Fax: <65>-538-6933/538-3877 URL: http://www.hitachi.com.sg

Hitachi Asia Ltd. (Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road, Hung-Kuo Building, Taipei (105), Taiwan

Fax: <886>-(2)-2718-8180 Telex: 23222 HAS-TP URL: http://www.hitachi.com.tw Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road Tsim Sha Tsui, Kowloon, Hong Kong

Tel: <852>-(2)-735-9218 Fax: <852>-(2)-730-0281 URL: http://www.hitachi.com.hk

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